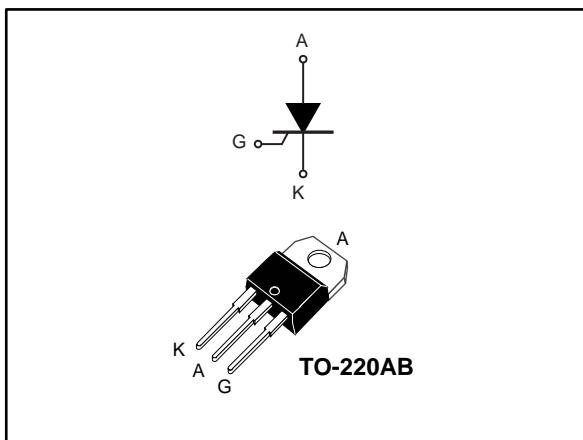


High temperature 50 A SCRs

Datasheet - production data



Description

Packaged in a non-isolated TO-220AB, this device offers high thermal performance during operation of up to 50 A, thanks to a junction temperature of up to 150 °C.

Its noise immunity ($dV/dt = 500 \text{ V}/\mu\text{s}$) trade-off versus gate triggering current ($I_{GT} = 15 \text{ mA}$) and its turn-on current rise ($dI/dt = 100 \text{ A}/\mu\text{s}$) allow the design of robust and compact control circuits for voltage regulators in motorbikes and industrial drives, overvoltage crowbar protection, motor control circuits in power tools and kitchen appliances, and inrush current-limiting circuits.

Features

- High junction temperature: $T_j = 150 \text{ }^\circ\text{C}$
- High noise immunity up to 150 °C
- Gate triggering current $I_{GT} = 15 \text{ mA}$
- Peak off-state voltage $V_{DRM}/V_{RRM} = 600 \text{ V}$
- High turn-on current rise $dI/dt = 100 \text{ A}/\mu\text{s}$
- ECOPACK®2 compliant component

Applications

- Motorbike voltage regulator circuits
- Inrush current limiting circuits
- Motor control circuits and starters
- Solid state relays

Table 1: Device summary

Order code	Package	V_{DRM}/V_{RRM}	I_{GT}
TN5015H-6T	TO-220AB	600 V	15 mA

1 Characteristics

Table 2: Absolute maximum ratings (limiting values), $T_j = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter		Value	Unit
$I_{T(\text{RMS})}$	RMS on-state current (180 ° conduction angle)	$T_c = 120^\circ\text{C}$	50	A
$I_{T(\text{AV})}$	Average on-state current (180 ° conduction angle)	$T_c = 122^\circ\text{C}$	30	A
		$T_c = 128^\circ\text{C}$	25	
		$T_c = 134^\circ\text{C}$	20	
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25 °C)	$t_p = 8.3 \text{ ms}$	493	A
		$t_p = 10 \text{ ms}$	450	
I^2t	I^2t value for fusing	$t_p = 10 \text{ ms}$	1012	A^2s
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \leq 100 \text{ ns}$	$f = 60 \text{ Hz}$	100	$\text{A}/\mu\text{s}$
V_{DRM}/V_{RRM}	Repetitive peak off-state voltage	$T_j = 150^\circ\text{C}$	600	V
V_{DSM}/V_{RSM}	Non repetitive surge peak off-state voltage	$t_p = 10 \text{ ms}$	$V_{DRM}/V_{RRM} + 100$	V
I_{GM}	Peak gate current	$t_p = 20 \mu\text{s}$	4	A
$P_{G(\text{AV})}$	Average gate power dissipation	$T_j = 150^\circ\text{C}$	1	W
V_{RGM}	Maximum peak reverse gate voltage		5	V
T_{stg}	Storage junction temperature range		-40 to +150	$^\circ\text{C}$
T_j	Maximum operating junction temperature		-40 to +150	$^\circ\text{C}$
T_l	Maximum lead temperature soldering during 10 s		260	$^\circ\text{C}$

Table 3: Electrical characteristics ($T_j = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Test conditions		Value	Unit	
I_{GT}	$V_D = 12 \text{ V}$, $R_L = 33 \Omega$	Max.	15	mA	
V_{GT}		Max.	1.3	V	
V_{GD}	$V_D = V_{DRM}$, $R_L = 3.3 \text{ k}\Omega$	$T_j = 150^\circ\text{C}$	Min.	0.15	V
I_H	$I_T = 500 \text{ mA}$, gate open		Max.	60	mA
I_L	$I_G = 1.2 \times I_{GT}$		Max.	80	mA
dV/dt	$V_D = 402 \text{ V}$, gate open	$T_j = 150^\circ\text{C}$	Min.	500	$\text{V}/\mu\text{s}$
t_{gt}	$I_{TM} = 100 \text{ A}$, $V_D = 402 \text{ V}$, $I_G = 30 \text{ mA}$, $(dI_G/dt)_{\text{max}} = 0.2 \text{ A}/\mu\text{s}$		Typ.	1.9	μs
t_q	$I_{TM} = 100 \text{ A}$, $V_D = 402 \text{ V}$, $(dI/dt)_{\text{off}} = 30 \text{ A}/\mu\text{s}$, $V_R = 25 \text{ V}$, $dV_D/dt = 50 \text{ V}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	Typ.	85	μs

Table 4: Static characteristics

Symbol	Test conditions			Value	Unit
V_{TM}	$I_{TM} = 100 \text{ A}$, $t_p = 380 \mu\text{s}$	$T_j = 25 \text{ }^\circ\text{C}$	Max.	1.65	V
V_{TO}	Threshold voltage	$T_j = 150 \text{ }^\circ\text{C}$	Max.	0.85	
R_D	Dynamic resistance	$T_j = 150 \text{ }^\circ\text{C}$	Max.	9	$\text{m}\Omega$
I_{DRM}, I_{RRM}	$V_D = V_{DRM} = V_{RRM}$	$T_j = 25 \text{ }^\circ\text{C}$	Max.	10	μA
		$T_j = 150 \text{ }^\circ\text{C}$		6	mA

Table 5: Thermal parameters

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case (DC)	Max.	0.6
$R_{th(j-a)}$	Junction to ambient (DC)	Typ.	${}^\circ\text{C/W}$

1.1 Characteristics (curves)

Figure 1: Maximum average power dissipation versus average on-state current

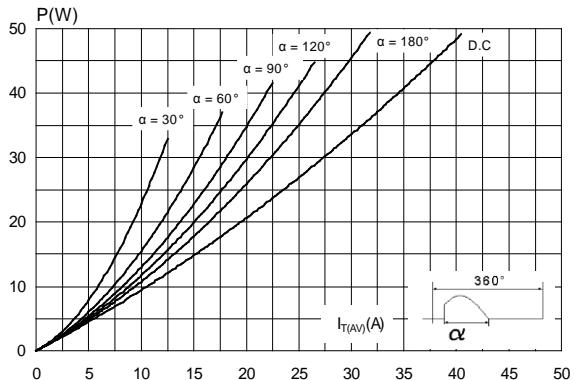


Figure 2: Average and DC on-state current versus case temperature

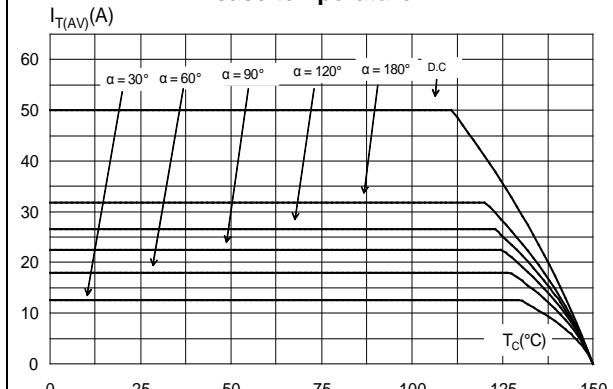


Figure 3: Average and D.C. on state current versus ambient temperature

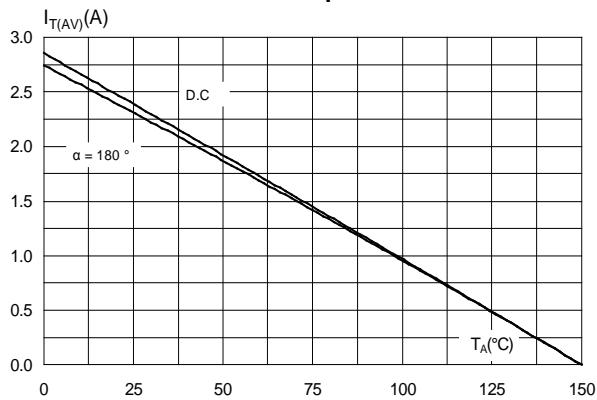


Figure 4: Relative variation of thermal impedance versus pulse duration

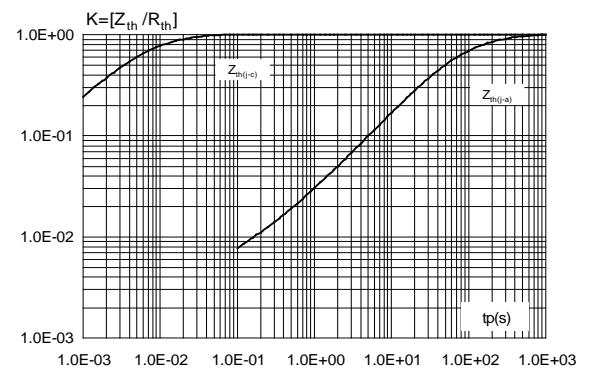


Figure 5: Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)

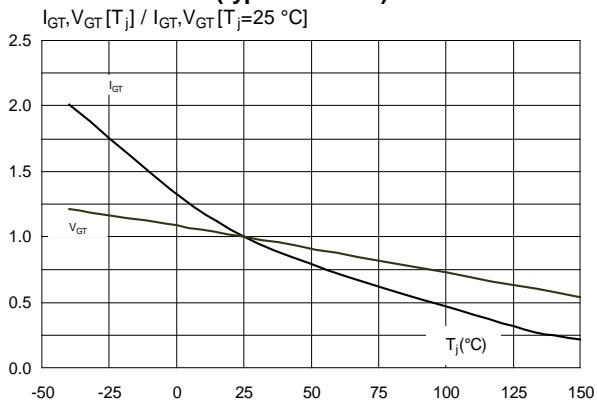
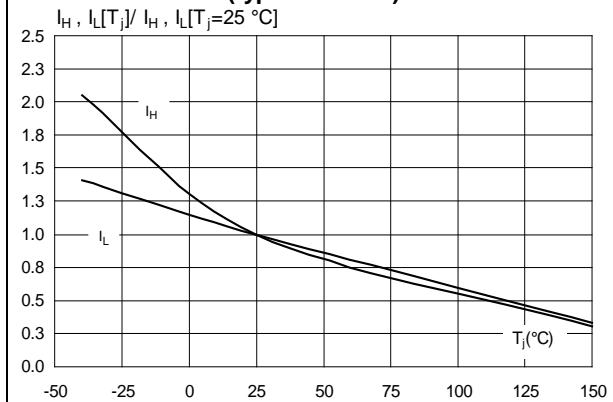


Figure 6: Relative variation of holding and latching current versus junction temperature (typical values)



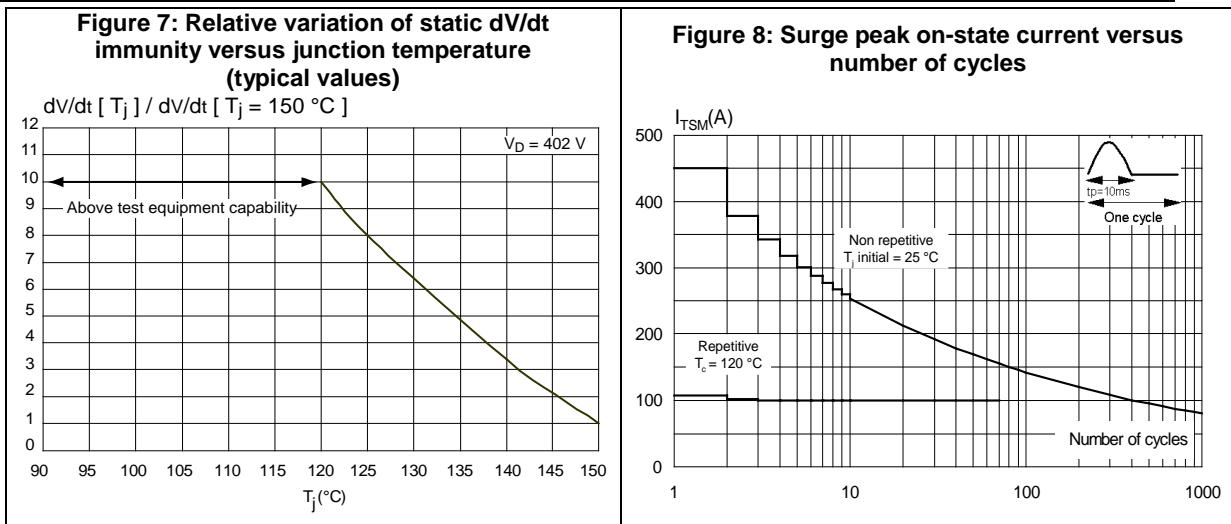


Figure 8: Surge peak on-state current versus number of cycles

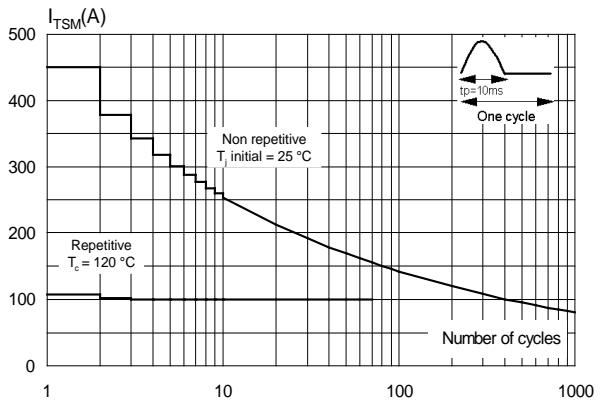


Figure 9: Non repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10 \text{ ms}$

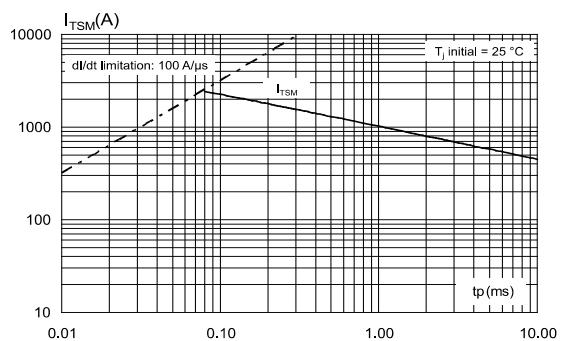


Figure 10: On-state characteristics (maximum values)

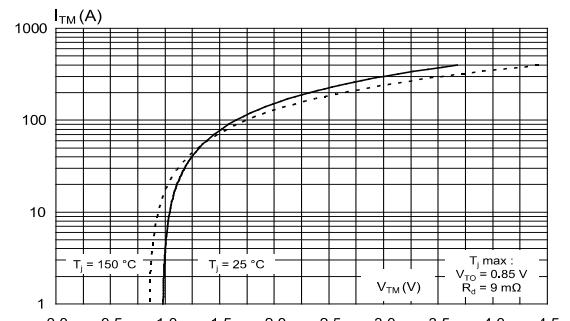
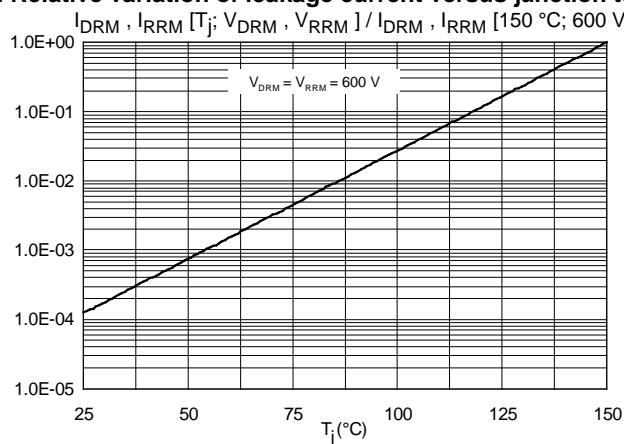


Figure 11: Relative variation of leakage current versus junction temperature



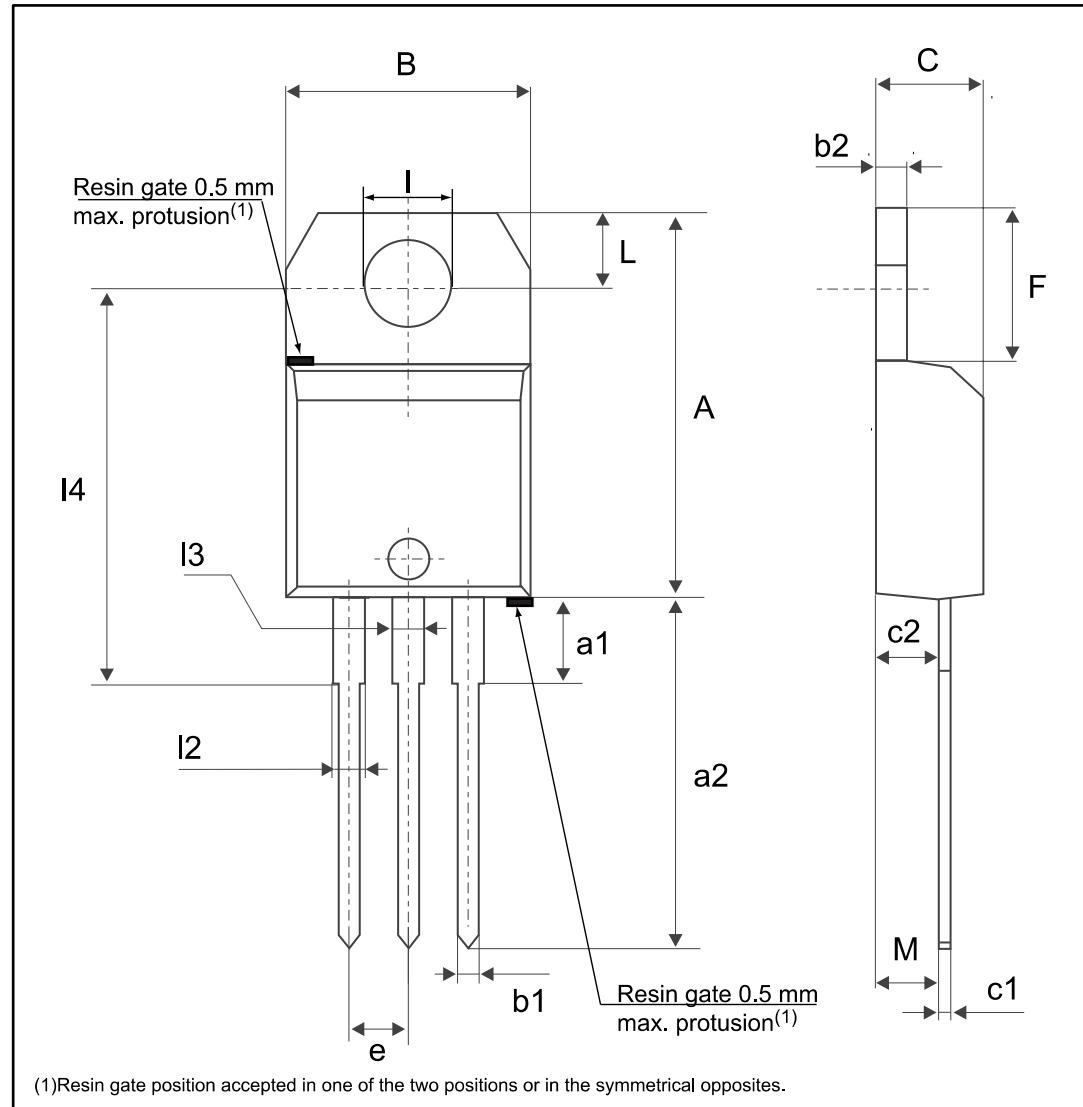
2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com.
ECOPACK® is an ST trademark.

- Epoxy meets UL94, V0
- Lead-free, halogen-free package

2.1 TO-220AB package information

Figure 12: TO-220AB (NIns. & Ins.) package outline



(1)Resin gate position accepted in one of the two positions or in the symmetrical opposites.

Table 6: TO-220AB (NIns. & Ins.) package mechanical data

Ref.	Dimensions					
	Millimeters			Inches ⁽¹⁾		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.5984		0.6260
a1		3.75			0.1476	
a2	13.00		14.00	0.5118		0.5512
B	10.00		10.40	0.3937		0.4094
b1	0.61		0.88	0.0240		0.0346
b2	1.23		1.32	0.0484		0.0520
C	4.40		4.60	0.1732		0.1811
c1	0.49		0.70	0.0193		0.0276
c2	2.40		2.72	0.0945		0.1071
e	2.40		2.70	0.0945		0.1063
F	6.20		6.60	0.2441		0.2598
I	3.73		3.88	0.1469		0.1528
L	2.65		2.95	0.1043		0.1161
I2	1.14		1.70	0.0449		0.0669
I3	1.14		1.70	0.0449		0.0669
I4	15.80	16.40	16.80	0.6220	0.6457	0.6614
M		2.6			0.1024	

Notes:

(1)Inch dimensions are for reference only.

3 Ordering information

Figure 13: Ordering information scheme

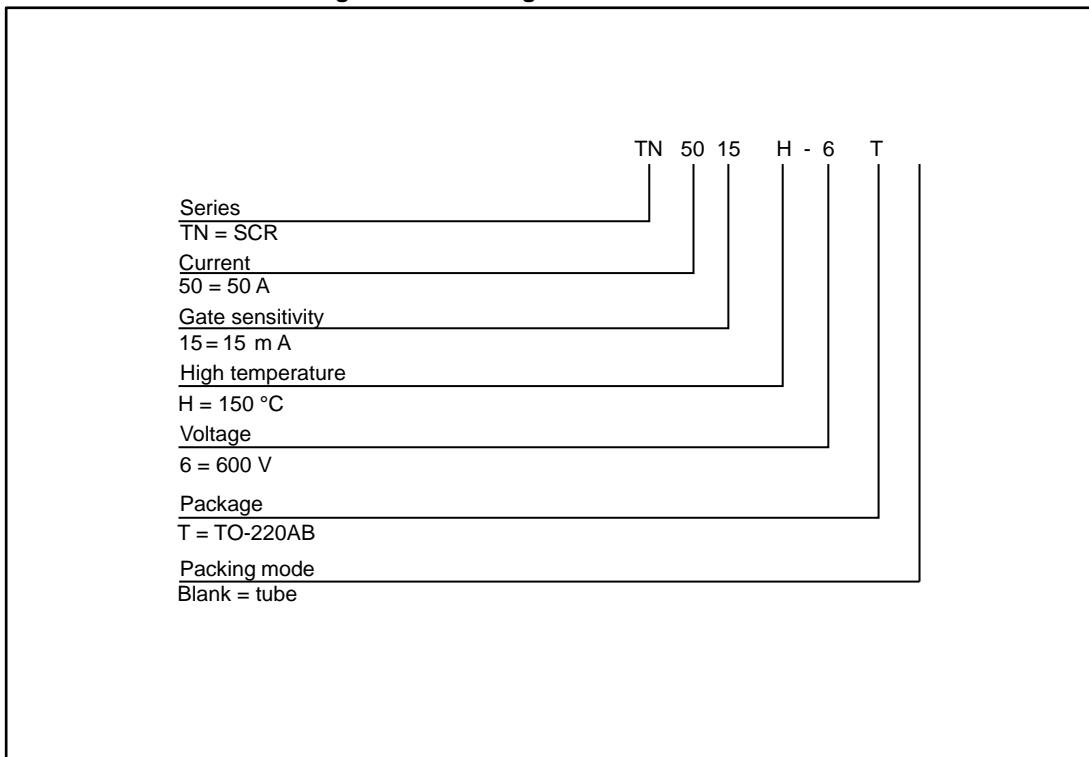


Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TN5015H-6T	TN5015H6	TO-220AB	2.3 g	50	Tube

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
01-Jun-2017	1	Initial release.

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